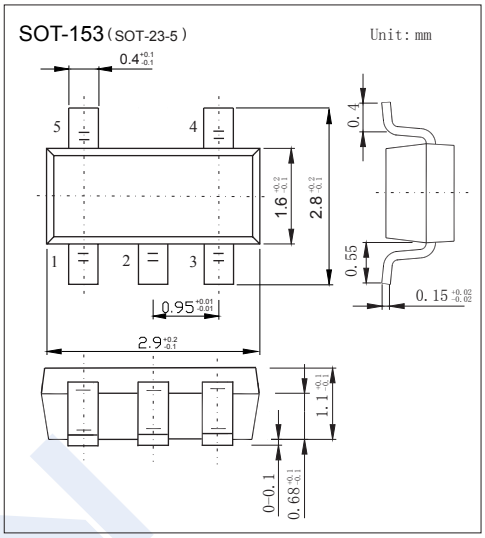
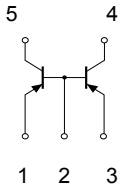
PNP Transistors

FMS4 (KMS4)



■ Features

- Collector Current Capability I_C=-50mA
- Collector Emitter Voltage V_{CEO}=-120V
- High breakdown voltage.



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-120	V
Collector - Emitter Voltage	V_{CEO}	-120	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-120			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B=0	-120			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -100 V , I_E=0			-0.5	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10 mA, I_B=-1mA			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-10 mA, I_B=-1mA			-1.2	
DC current gain	h_{FE}	V_{CE}= -6V, I_C= -2mA	180		820	
Transition frequency	f_T	V_{CE}= -12V, I_E= 2mA,f=100MHz		140		MHz

■ Marjking

Marking	S4